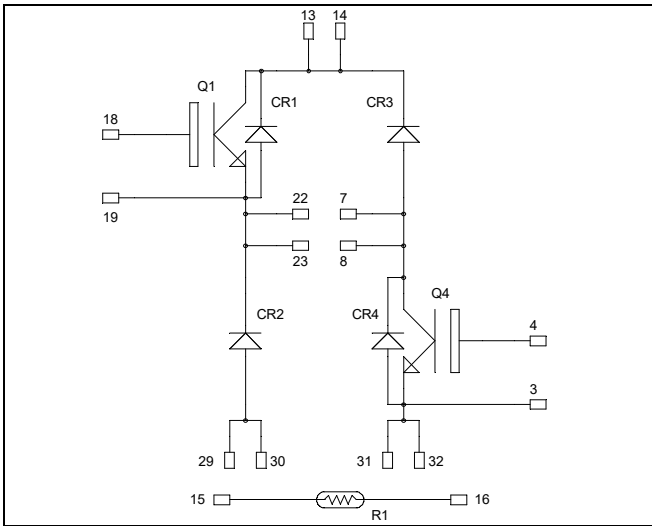


**Asymmetrical - Bridge
Trench + Field Stop IGBT3
Power Module**

**$V_{CES} = 1200V$
 $I_C = 75A @ T_c = 80^\circ C$**

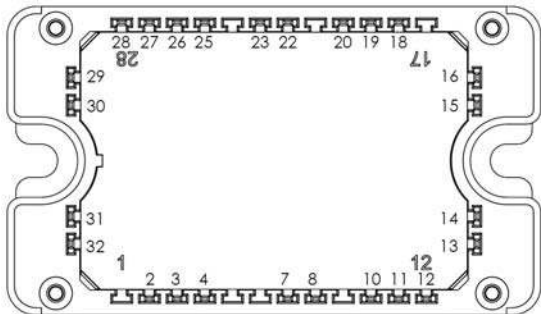


Application

- Welding converters
- Switched Mode Power Supplies
- Switched Reluctance Motor Drives

Features

- **Trench + Field Stop IGBT3**
 - Low voltage drop
 - Low tail current
 - Low diode VF
 - Low leakage current
 - RBSOA and SCSOA rated
- Kelvin emitter for easy drive
- Very low stray inductance
- Internal thermistor for temperature monitoring



Benefits

- Outstanding performance at high frequency operation
- Direct mounting to heatsink (isolated package)
- Low junction to case thermal resistance
- Solderable terminals both for power and signal for easy PCB mounting
- Low profile
- RoHS Compliant

All multiple inputs and outputs must be shorted together
 Example: 13/14 ; 29/30 ; 22/23 ...

All ratings @ $T_j = 25^\circ C$ unless otherwise specified

Absolute maximum ratings (per IGBT)

Symbol	Parameter	Max ratings	Unit
V_{CES}	Collector - Emitter Voltage	1200	V
I_C	Continuous Collector Current	$T_C = 25^\circ C$	110
		$T_C = 80^\circ C$	75
I_{CM}	Pulsed Collector Current	$T_C = 25^\circ C$	175
V_{GE}	Gate - Emitter Voltage	± 20	V
P_D	Power Dissipation	$T_C = 25^\circ C$	357
RBSOA	Reverse Bias Safe Operating Area	$T_j = 125^\circ C$	150A @ 1150V

CAUTION: These Devices are sensitive to Electrostatic Discharge. Proper Handling Procedures Should Be Followed.

Electrical Characteristics (per IGBT)

Symbol	Characteristic	Test Conditions	Min	Typ	Max	Unit
I _{CEs}	Zero Gate Voltage Collector Current	V _{GE} = 0V, V _{CE} = 1200V			250	μA
V _{CE(sat)}	Collector Emitter saturation Voltage	V _{GE} = 15V I _C = 75A	T _j = 25°C 1.4	T _j = 25°C 1.7 T _j = 125°C 2.0	2.1	V
V _{GE(th)}	Gate Threshold Voltage	V _{GE} = V _{CE} , I _C = 3 mA	5.0		6.5	V
I _{GES}	Gate – Emitter Leakage Current	V _{GE} = 20V, V _{CE} = 0V			400	nA

Dynamic Characteristics (per IGBT)

Symbol	Characteristic	Test Conditions	Min	Typ	Max	Unit
C _{ies}	Input Capacitance	V _{GE} = 0V		5340		pF
C _{oes}	Output Capacitance	V _{CE} = 25V		280		
C _{res}	Reverse Transfer Capacitance	f = 1MHz		240		
Q _G	Gate charge	V _{GE} = ±15V, I _C = 75A V _{CE} = 600V		0.7		μC
T _{d(on)}	Turn-on Delay Time	Inductive Switching (25°C) V _{GE} = ±15V V _{Bus} = 600V I _C = 75A R _G = 4.7Ω		260		ns
T _r	Rise Time			30		
T _{d(off)}	Turn-off Delay Time			420		
T _f	Fall Time			70		
T _{d(on)}	Turn-on Delay Time	Inductive Switching (125°C) V _{GE} = ±15V V _{Bus} = 600V I _C = 75A R _G = 4.7Ω		285		ns
T _r	Rise Time			50		
T _{d(off)}	Turn-off Delay Time			520		
T _f	Fall Time			90		
E _{on}	Turn-on Switching Energy	V _{GE} = ±15V V _{Bus} = 600V	T _j = 125°C	7		mJ
E _{off}	Turn-off Switching Energy	I _C = 75A R _G = 4.7Ω	T _j = 125°C	8.1		
I _{sc}	Short Circuit data	V _{GE} ≤ 15V ; V _{Bus} = 900V t _p ≤ 10μs ; T _j = 125°C		300		A
R _{thJC}	Junction to Case Thermal Resistance				0.35	°C/W

Diode ratings and characteristics (CR2 & CR3) (per diode)

Symbol	Characteristic	Test Conditions	Min	Typ	Max	Unit
V _{RRM}	Peak Repetitive Reverse Voltage				1200	V
I _{RM}	Reverse Leakage Current	V _R = 1200V			250	μA
I _F	DC Forward Current		T _c = 80°C	75		A
V _F	Diode Forward Voltage	I _F = 75A	T _j = 25°C 1.6	T _j = 25°C 1.6 T _j = 125°C 2.1		V
t _{rr}	Reverse Recovery Time	I _F = 75A V _R = 600V di/dt = 2000A/μs	T _j = 25°C	170		ns
			T _j = 125°C	280		
Q _{rr}	Reverse Recovery Charge		T _j = 25°C	7		μC
			T _j = 125°C	14		
E _r	Reverse Recovery Energy		T _j = 25°C 3			mJ
			T _j = 125°C 5.5			
R _{thJC}	Junction to Case Thermal Resistance				0.58	°C/W

CR1 & CR4 are IGBT protection diodes only

Thermal and package characteristics

Symbol	Characteristic	Min	Max	Unit		
V _{ISOL}	RMS Isolation Voltage, any terminal to case t=1 min, 50/60Hz	4000		V		
T _J	Operating junction temperature range	-40	150	°C		
T _{JOP}	Recommended junction temperature under switching conditions	-40	T _{Jmax} -25			
T _{STG}	Storage Temperature Range	-40	125			
T _C	Operating Case Temperature	-40	125			
Torque	Mounting torque	To Heatsink	M5	2	3	N.m
Wt	Package Weight				110	g

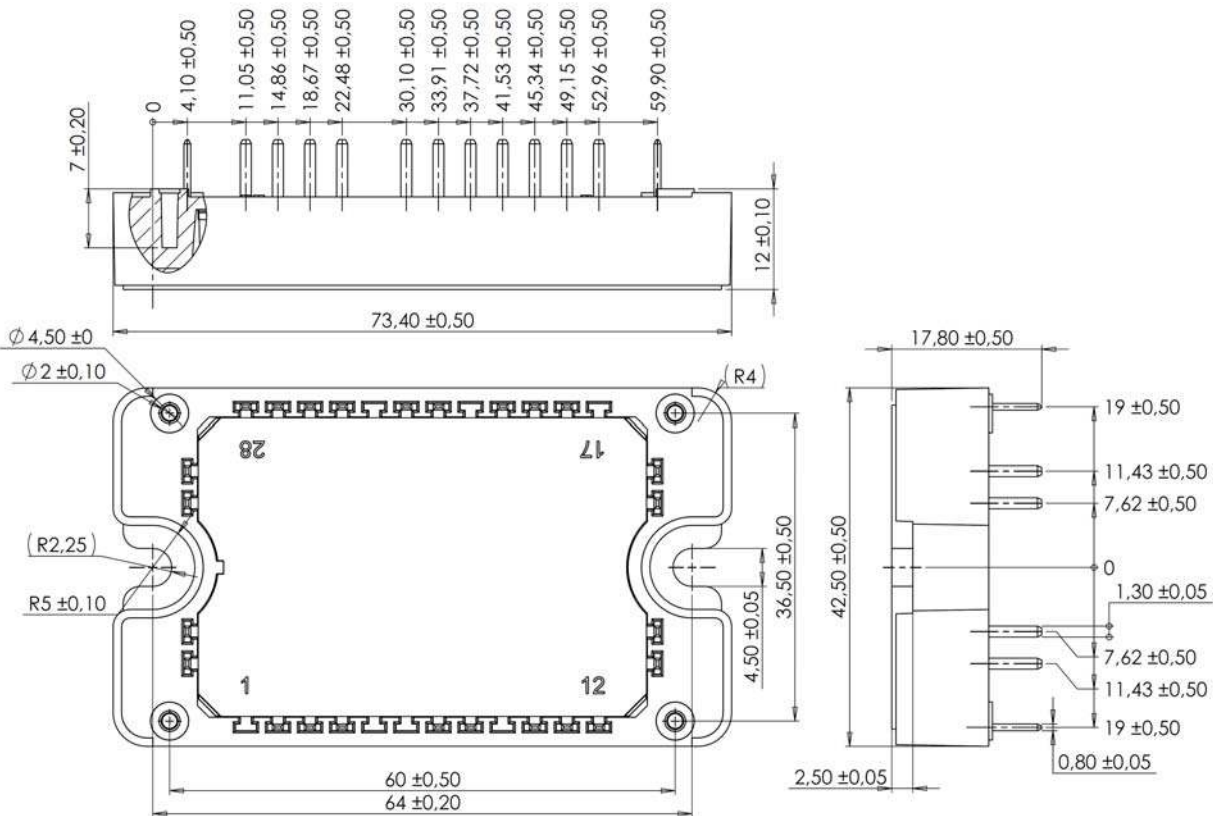
Temperature sensor NTC (see application note APT0406 on www.microsemi.com for more information).

Symbol	Characteristic	Min	Typ	Max	Unit
R ₂₅	Resistance @ 25°C		50		kΩ
ΔR ₂₅ /R ₂₅			5		%
B _{25/85}	T ₂₅ = 298.15 K		3952		K
ΔB/B		T _C = 100°C	4		%

$$R_T = \frac{R_{25}}{\exp \left[B_{25/85} \left(\frac{1}{T_{25}} - \frac{1}{T} \right) \right]}$$

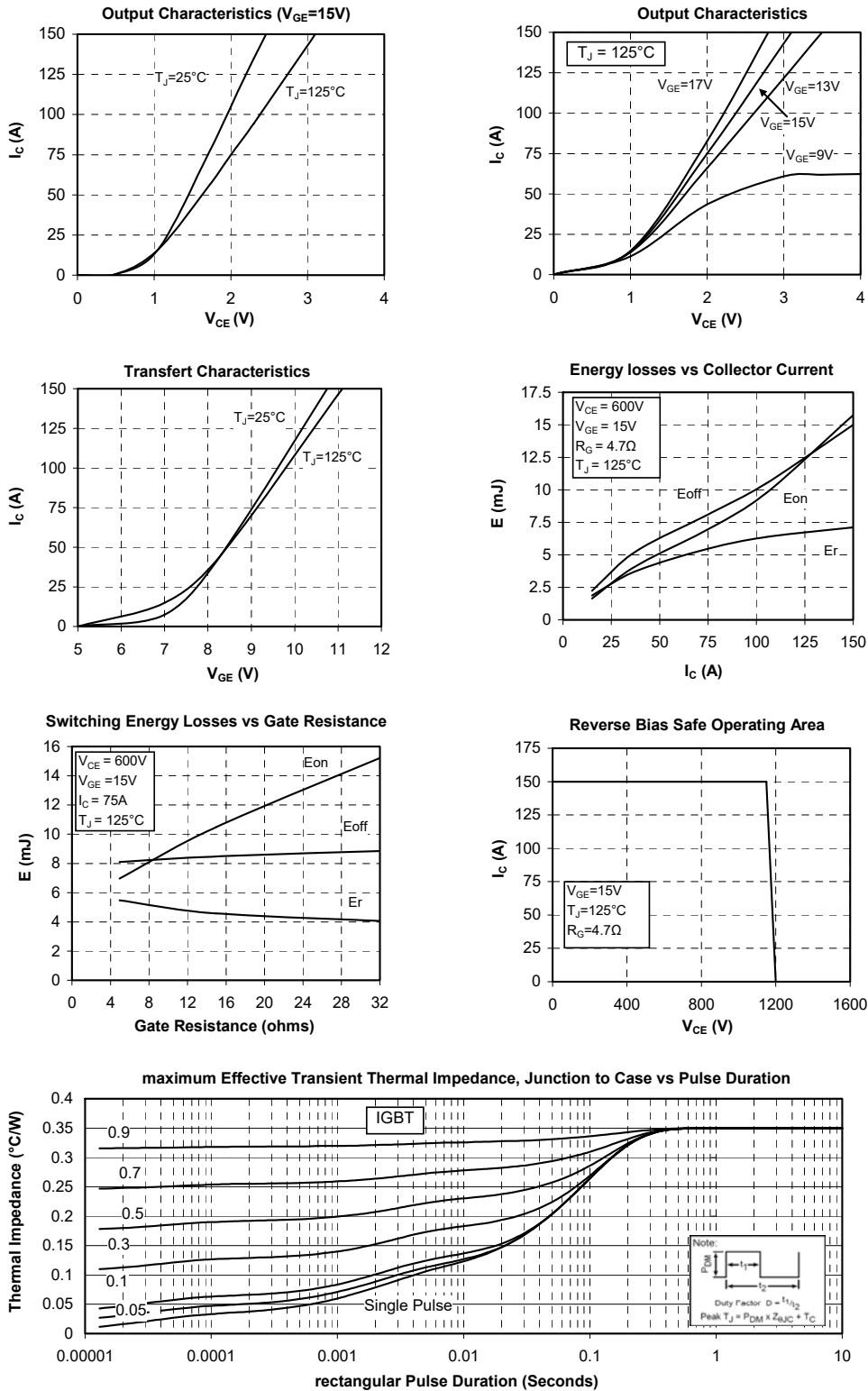
T: Thermistor temperature
 R_T: Thermistor value at T

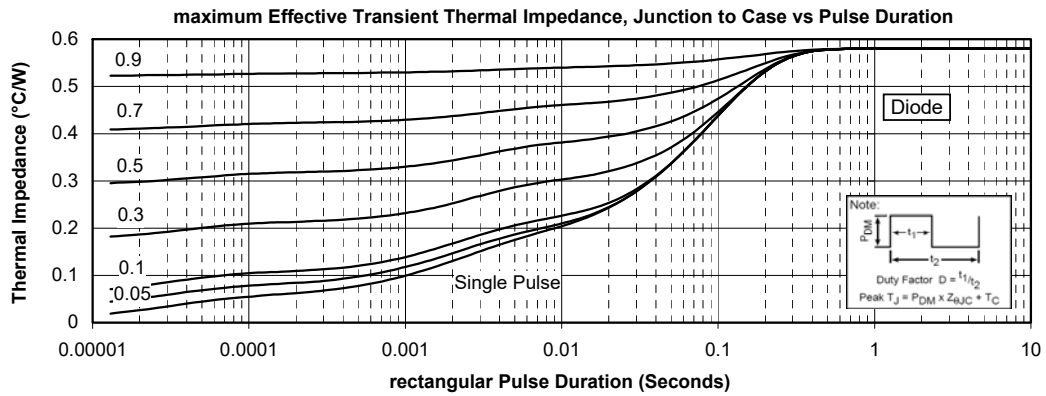
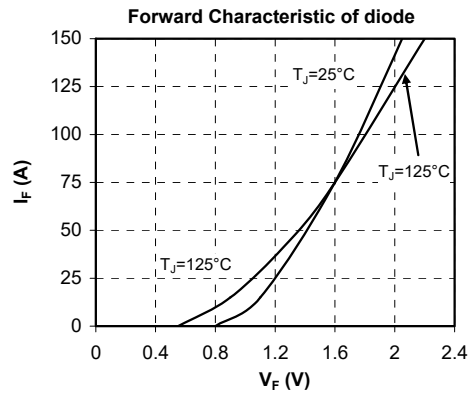
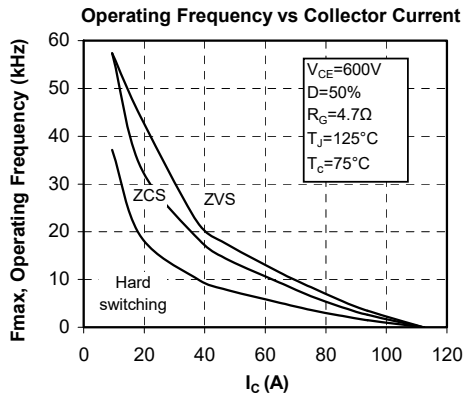
Package outline (dimensions in mm)



See application note 1906 - Mounting Instructions for SP3F Power Modules on www.microsemi.com

Typical Performance Curve





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